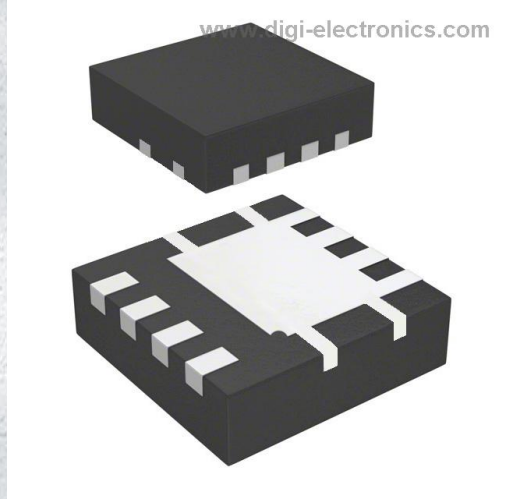
DMN3029LFG-13 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	DMN3029LFG-13-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN3029LFG-13
Description	MOSFET N-CH 30V 5.3A PWRDI333-8
Detailed Description	N-Channel 30 V 5.3A (Ta) 1W (Ta) Surface Mount PO WERDI3333-8

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN3029LFG-13	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	5.3A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	18.6mOhm @ 10A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.8V @ 250µA	11.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±25V	580 pF @ 15 V
FET Feature:	Power Dissipation (Max):
-	1W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI3333-8	8-PowerVDFN
Base Product Number:	
DMN3029	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

DMN3029LFG

N-CHANNEL ENHANCEMENT MODE MOSFET
POWERDI®

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = 25°C
30V	18.6mΩ @ V_{GS} = 10V	8.0A
	26.5mΩ @ V_{GS} = 4.5V	6.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- DC-DC Converters
- Power management functions

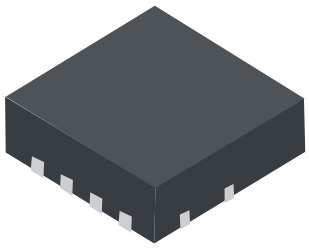
Features

- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- 100% Rg tested
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

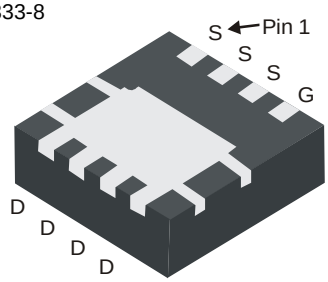
Mechanical Data

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (approximate)

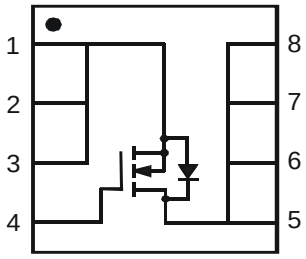
POWERDI3333-8



Top View



Bottom View



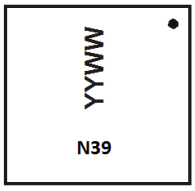
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3029LFG-7	POWERDI3333-8	2000 / Tape & Reel
DMN3029LFG-13	POWERDI3333-8	3000 / Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



N39 = Product marking code
YYWW = Date code marking
YY = Last digit of year (ex: 10 for 2010)
WW = Week code (01 – 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.3 4.2	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	8.0 6.3	A
Continuous Drain Current (Note 6) V_{GS} = 10V	t ≤ 10s	T_A = +25°C T_A = +70°C	I_D	9.5 7.7	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	6.5 4.9	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	t ≤ 10s	T_A = +25°C T_A = +70°C	I_D	7.8 6.2	A
Pulsed Drain Current (Note 7)			I_{DM}	70	A
Avalanche Current (Notes 7 & 8)			I_{AR}	18	A
Repetitive Avalanche Energy (Notes 7 & 8) L = 0.1mH			E_{AR}	16	mJ

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_D	1.0	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	130.6	°C/W
Power Dissipation (Note 6)	P_D	2.07	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6)	$R_{\theta JA}$	62.5	°C/W
Power Dissipation (Note 6) t ≤ 10s	P_D	3.0	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 6) t ≤ 10s	$R_{\theta JA}$	43.8	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
7. Repetitive rating, pulse width limited by junction temperature.
8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C.

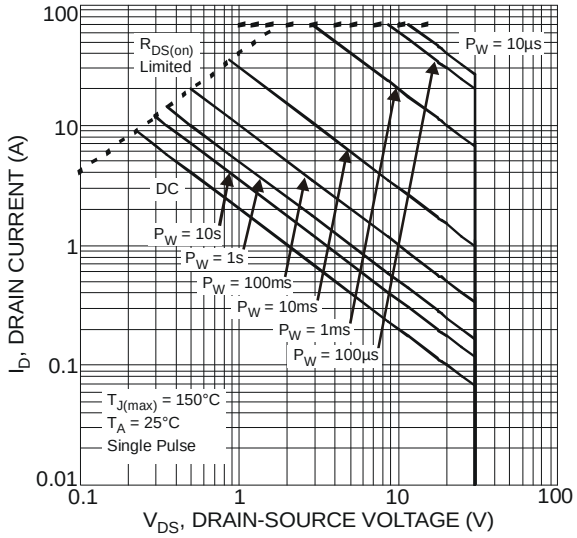


Fig. 1 SOA, Safe Operation Area

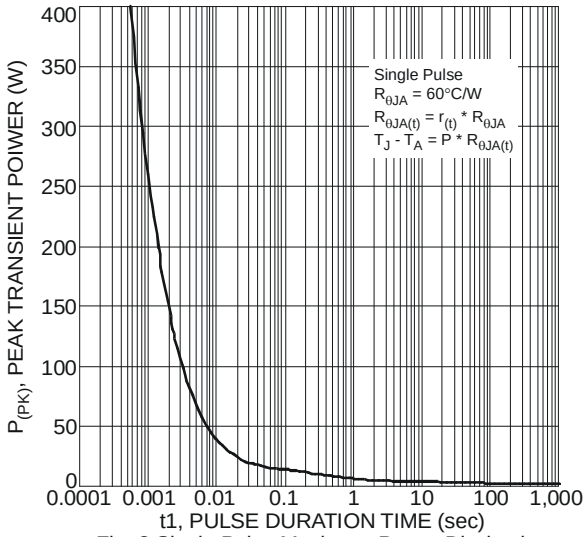


Fig. 2 Single Pulse Maximum Power Dissipation

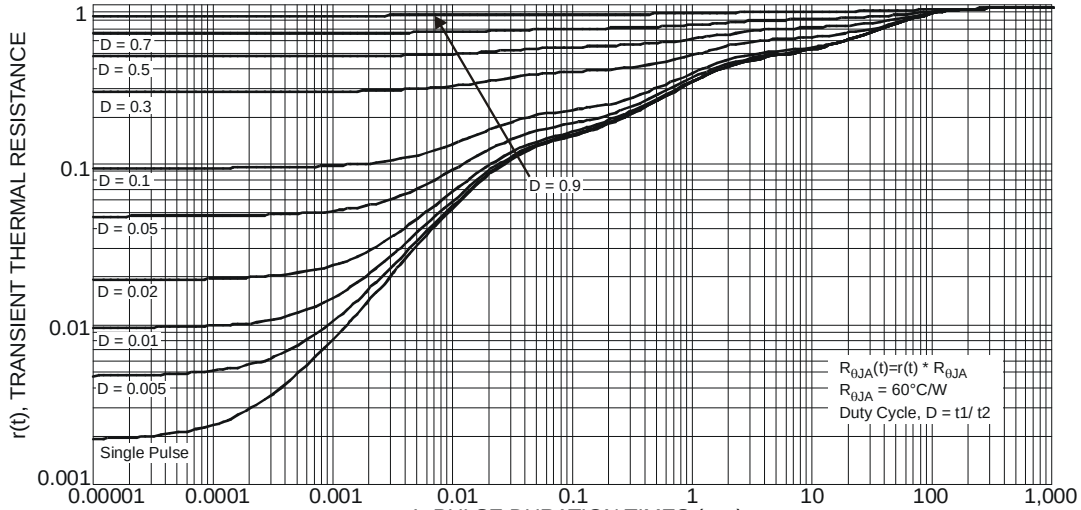


Fig. 3 Transient Thermal Resistance

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	0.1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±25V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(th)}$	0.9	1.2	1.8	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	13,5	18.6	mΩ	V_{GS} = 10V, I_D = 10A
		-	22	26.5		V_{GS} = 4.5V, I_D = 7.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	13.0	-	S	V_{DS} = 5V, I_D = 10A
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	-	580	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	110	-		
Reverse Transfer Capacitance	C_{rss}	-	70	-		
Gate Resistance	R_g	-	2.0	3.0	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge V_{GS} = 4.5V	Q_g	-	5.3	-	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 10A
Total Gate Charge V_{GS} = 10V	Q_g	-	11.3	-		V_{GS} = 10V, V_{DS} = 15V, I_D = 10A
Gate-Source Charge	Q_{gs}	-	1.9	-		
Gate-Drain Charge	Q_{gd}	-	1.9	-		
Turn-On Delay Time	$t_{D(on)}$	-	4.4	-	ns	V_{GS} = 10V, V_{DS} = 15V, R_L = 15Ω, R_G = 6Ω
Turn-On Rise Time	t_r	-	4.6	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	19.5	-	ns	
Turn-Off Fall Time	t_f	-	5.8	-	ns	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to production testing.

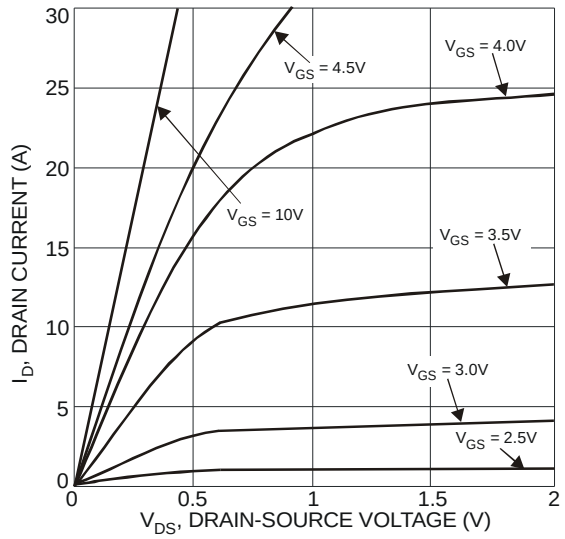


Fig. 4 Typical Output Characteristic

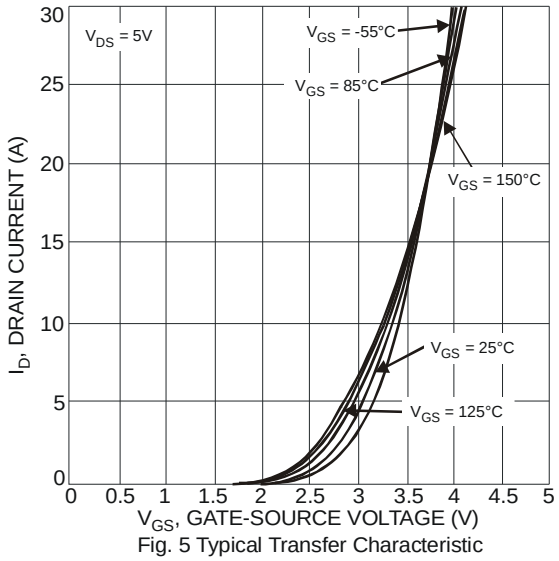


Fig. 5 Typical Transfer Characteristic

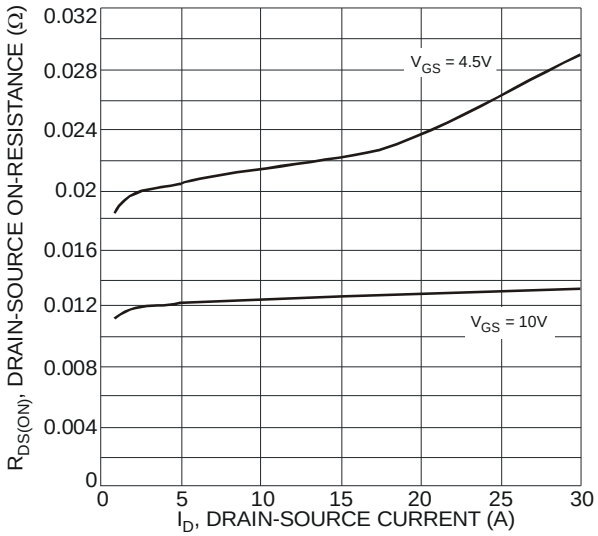


Fig. 6 Typical On-Resistance
vs. Drain Current and Gate Voltage

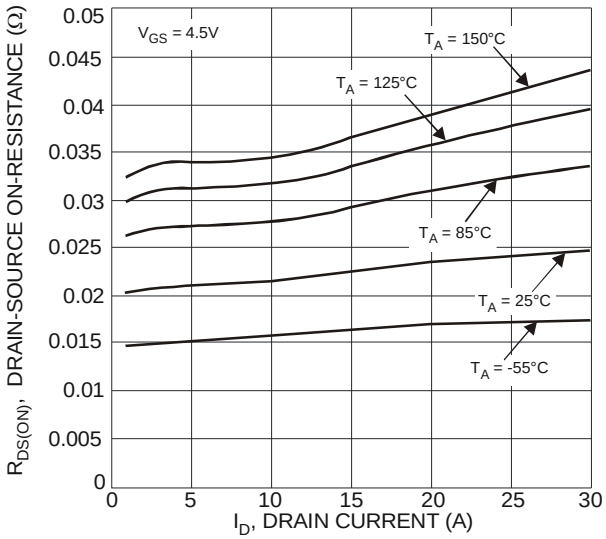


Fig. 7 Typical On-Resistance
vs. Drain Current and Temperature

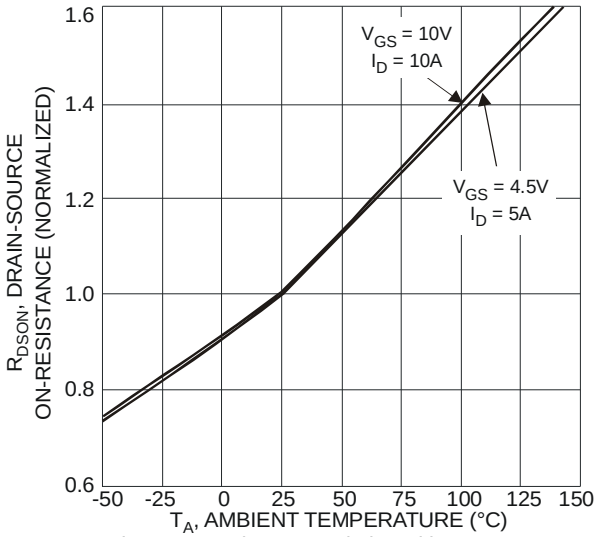


Fig. 8 On-Resistance Variation with Temperature

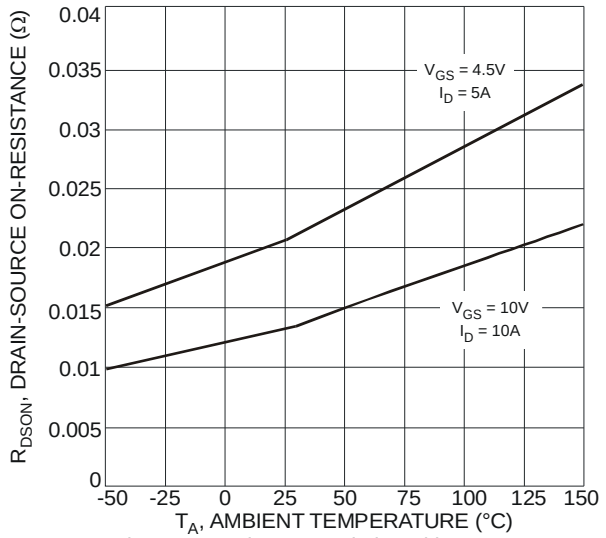


Fig. 9 On-Resistance Variation with Temperature

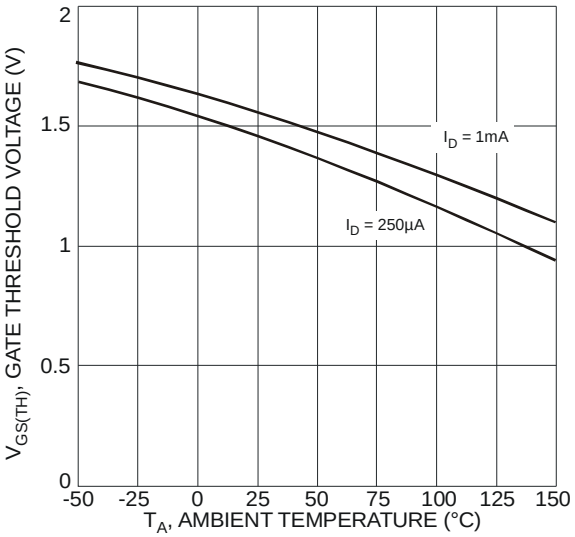


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

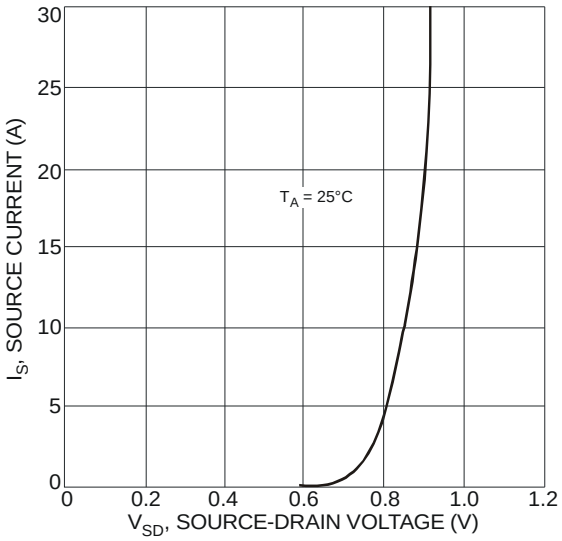


Fig. 11 Diode Forward Voltage vs. Current

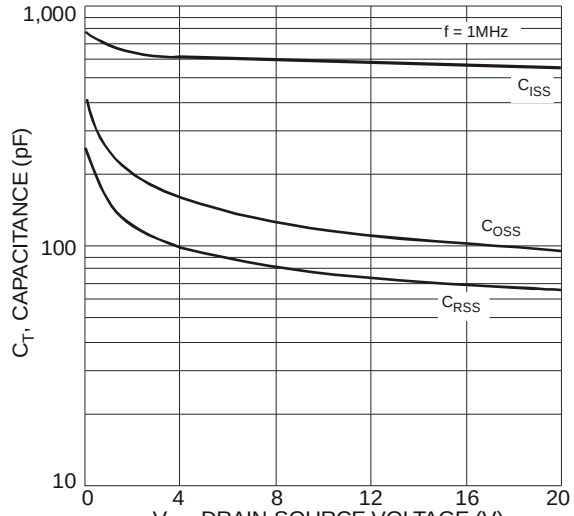


Fig. 12 Typical Total Capacitance

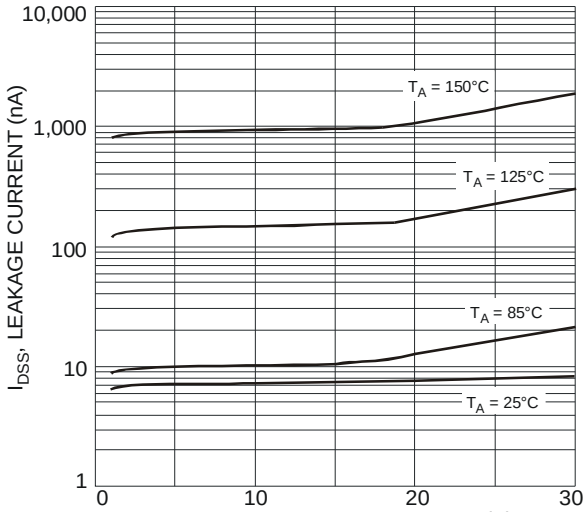
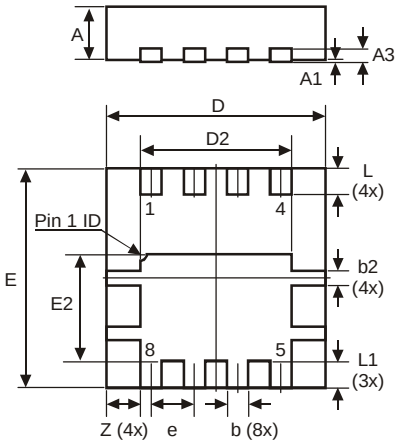


Fig. 13 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

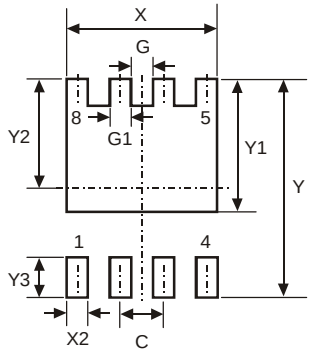
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI3333-8			
Dim	**Min**	**Max**	**Typ**
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
L	0.35	0.45	0.40
L1	–	–	0.39
e	–	–	0.65
Z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

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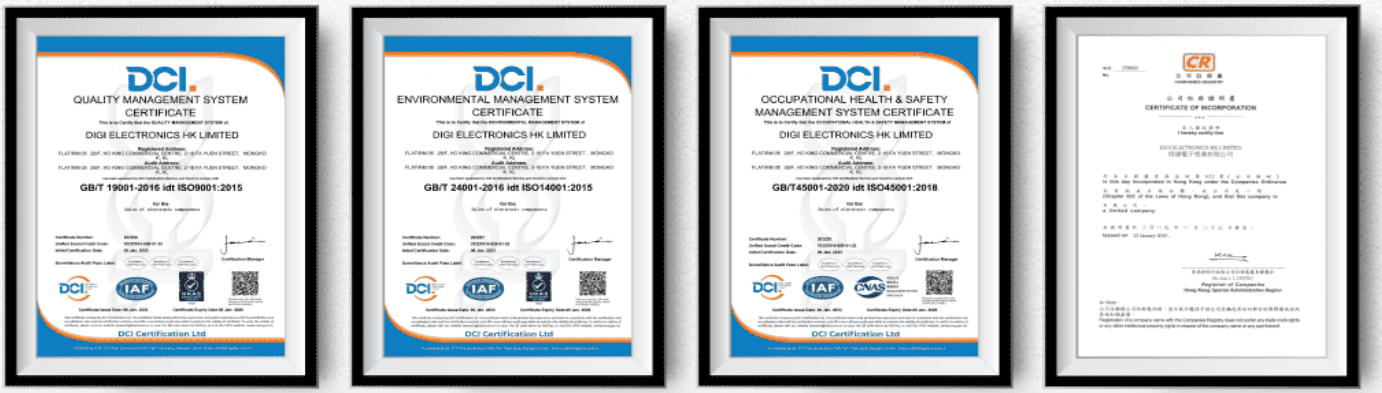

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